

Features

- Dual N-Channel MOSFET
- Low On-Resistance
 - 100mΩ @V_{GS} = 4.5V, I_D = 2.5A
 - 140mΩ @V_{GS} = 2.5V, I_D = 1.5A
 - 215mΩ @V_{GS} = 1.8V, I_D = 1A
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate to 2kV HBM
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

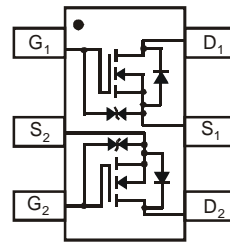


ESD PROTECTED TO 2KV



TOP VIEW

SOT-26



TOP VIEW

Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	20	V
Gate-Source Voltage	V _{GSS}	±12	V
Drain Current (Note 1)	I _D	T _A = 25°C	2.0
		T _A = 85°C	1.4
Pulsed Drain Current (Note 4)	I _{DM}	7.0	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P _D	650	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	192	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Notes:
1. Device mounted on FR-4 PCB, or minimum recommended pad layout
 2. No purposefully added lead.
 3. Detail go to our website at www.twtysemi.com
 4. Pulse width ≤ 10μs, duty cycle ≤ 1%.